Åukasz Gelczuk

List of Publications by Year
in descending order

#	ARTICLE	IF	CITATIONS
1	Characterization of deep electron traps in 4H-SiC Junction Barrier Schottky rectifiers. Solid-State Electronics, 2014, 94, 56-60.	0.8	37
2	Deep-level defects in n-type GaAsBi alloys grown by molecular beam epitaxy at low temperature and their influence on optical properties. Scientific Reports, 2017, 7, 12824.	1.6	31
3	Anisotropic misfit strain relaxation in lattice mismatched InGaAs/GaAs heterostructures grown by MOVPE. Journal of Crystal Growth, 2008, 310, 3014-3018.	0.7	16
4	Correlation between barrier inhomogeneities of 4H-SiC 1A/600V Schottky rectifiers and deep-level defects revealed by DLTS and Laplace DLTS. Solid-State Electronics, 2014, 99, 1-6.	0.8	16
5	Bi-induced acceptor level responsible for partial compensation of native free electron density in InP1âˆ'xBixdilute bismide alloys. Journal Physics D: Applied Physics, 2016, 49, 115107.	1.3	14
6	Identification of nitrogen- and host-related deep-level traps in n-type GaNAs and their evolution upon annealing. Journal of Applied Physics, 2014, 116, 013705.	1.1	12
7	Electronic states at misfit dislocations in partially relaxed InGaAs/GaAs heterostructures. Physica B: Condensed Matter, 2007, 388, 195-199.	1.3	11
8	Origin and annealing of deep-level defects in GaNAs grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	9
9	Characterization of deep-level defects in GaNAs/GaAs heterostructures grown by APMOVPE. Materials Science-Poland, 2016, 34, 726-734.	0.4	9
10	Origin and anomalous behavior of dominant defects in 4H-SiC studied by conventional and Laplace deep level transient spectroscopy. Journal of Applied Physics, 2020, 127, .	1.1	7
11	Influence of the AP MOVPE process parameters on properties of (In, Ga)(As, N)/ GaAs heterostructures for photovoltaic applications. Proceedings of SPIE, 2013, , .	0.8	6
12	Structural Characterization of Doped Thick Gainnas Layers - Ambiguities and Challenges. Journal of Electrical Engineering, 2014, 65, 299-303.	0.4	5
13	DLTS Investigations of (Ga,In)(N,As)/GaAs Quantum Wells before and after Rapid Thermal Annealing. Acta Physica Polonica A, 2014, 126, 1195-1198.	0.2	4
14	Anisotropy of strain relaxation in heterogeneous GaInNAs layers grown by AP-MOVPE. Journal of Crystal Growth, 2015, 430, 14-20.	0.7	4
15	Dislocation-related electronic states in partially strain-relaxed InGaAs/GaAs heterostructures grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 3037-3042.	0.8	3
16	Misfit dislocations and surface morphology of InGaAs/GaAs heterostructures grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1918-1921.	0.8	3
17	Probing Defects in MoS 2 Van der Waals Crystal through Deepâ€Level Transient Spectroscopy. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000381.	1.2	3
18	Investigation of deep-level defects in InGaAsN/GaAs 3xQWs structures grown by AP-MOVPE. , 2013, , .		2

#	Article	IF	Citations
19	Deep traps and optical properties of partially strain-relaxed InGaAs/GaAs heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 166-170.	1.7	1
20	Electrically active defects in SiC Schottky barrier diodes. Materials Science-Poland, 2011, 29, 70-75.	0.4	1
21	Deep Level Defects in 4H-SiC Schottky Diodes Examined by DLTS. Solid State Phenomena, 0, 178-179, 366-371.	0.3	1
22	DLTS and PR Studies of Partially Relaxed InGaAs/GaAs Heterostructures Grown by MOVPE. Solid State Phenomena, 2007, 131-133, 485-490.	0.3	0
23	High resolution transient analysis for â€œlocalizedâ€•states at the extended defects in InGaAs/GaAs heterostructures grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2888-2892.	0.8	0
24	Strain relaxation induced surface morphology of heterogeneous GaInNAs layers grown on GaAs substrate. Journal of Crystal Growth, 2017, 470, 108-112.	0.7	0